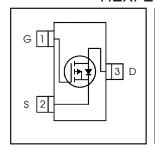
International Rectifier

IRLML2244TRPbF

HEXFET® Power MOSFET

V _{DS}	-20	V
V _{GS Max}	± 12	٧
$R_{DS(on) max}$ (@V _{GS} = -4.5V)	54	$\mathbf{m}\Omega$
$R_{DS(on) max}$ (@V _{GS} = -2.5V)	95	$\mathbf{m}\Omega$





Application(s)

System/Load Switch

Features and Benefits

Features

Low $R_{DS(on)}$ ($\leq 54m\Omega$)
Industry-standard pinout
Compatible with existing Surface Mount Techniques
RoHS compliant containing no lead, no bromide and no halogen
MSL1, Consumer qualification

Benefits

	Lower switching losses
	Multi-vendor compatibility
results in	Easier manufacturing
\Rightarrow	Environmentally friendly
	Increased reliability

Absolute Maximum Ratings

Absolute Maximum natings					
Symbol Parameter		Max.	Units		
V _{DS}	Drain-Source Voltage	-20	V		
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ -4.5V	-4.3			
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ -4.5V	-3.4	Α		
I _{DM}	Pulsed Drain Current	-18			
P _D @T _A = 25°C	Maximum Power Dissipation	1.3	w		
P _D @T _A = 70°C Maximum Power Dissipation		0.8	T vv		
	Linear Derating Factor	0.01	W/°C		
V _{GS}	Gate-to-Source Voltage	± 12	V		
T _{J,} T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C		

Thermal Resistance

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③		100	°C/W
$R_{\theta JA}$	Junction-to-Ambient (t<10s) ®		99	C/VV

ORDERING INFORMATION:

See detailed ordering and shipping information on the last page of this data sheet.

Notes ① through ④ are on page 10 www.irf.com

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Electric Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-20			٧	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient		0.01		V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance		42	54	mΩ	V _{GS} = -4.5V, I _D = -4.3A ②
1 1DS(on)	Static Dialific-Source Off-nesistatice		71	95	11122	V _{GS} = -2.5V, I _D = -3.4A ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.4		-1.1	>	$V_{DS} = V_{GS}$, $I_D = -10\mu A$
I _{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS} = -16V, V_{GS} = 0V$
	Diam-to-Source Leakage Current			150	μΑ	$V_{DS} = -16V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage	_	_	-100	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage		_	100	IIA	V _{GS} = -12V
R_{G}	Internal Gate Resistance		8.9		Ω	
gfs	Forward Transconductance	6.5			S	$V_{DS} = -10V, I_{D} = -4.3A$
Q_g	Total Gate Charge		6.9			$I_D = -4.3A$
Q_{gs}	Gate-to-Source Charge		1.0		nC	V _{DS} =-10V
Q_{gd}	Gate-to-Drain ("Miller") Charge		2.9			V _{GS} = -4.5V ②
t _{d(on)}	Turn-On Delay Time		7.0			V _{DD} =-10V②
t _r	Rise Time		12			I _D = -1A
t _{d(off)}	Turn-Off Delay Time		34		ns	$R_G = 6.8\Omega$
t _f	Fall Time		25			V _{GS} = -4.5V
C _{iss}	Input Capacitance		570			V _{GS} = 0V
C _{oss}	Output Capacitance		160		pF	V _{DS} = -16V
C _{rss}	Reverse Transfer Capacitance		110			f = 1.0KHz

Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			-1.3		MOSFET symbol
	(Body Diode)			-1.0	A	showing the
I _{SM}	Pulsed Source Current			-18		integral reverse
	(Body Diode) ①			-10		p-n junction diode.
V_{SD}	Diode Forward Voltage			-1.2	٧	$T_J = 25^{\circ}C$, $I_S = -4.3A$, $V_{GS} = 0V$ ②
t _{rr}	Reverse Recovery Time		21	32	ns	$T_J = 25^{\circ}C$, $V_R = -16V$, $I_F = -4.3A$
Q _{rr}	Reverse Recovery Charge		9.0	14	nC	di/dt = 100A/µs ②

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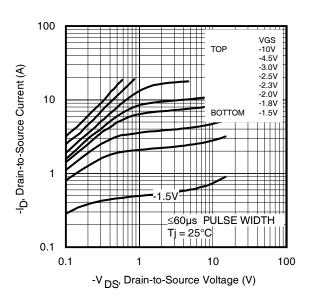


Fig 1. Typical Output Characteristics

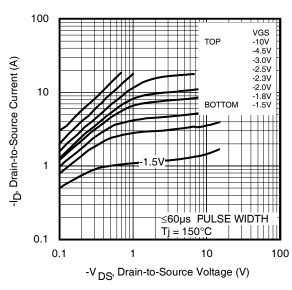


Fig 2. Typical Output Characteristics

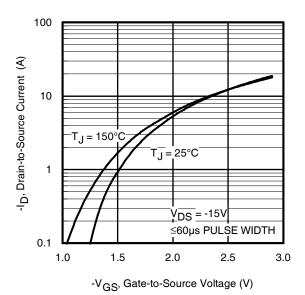


Fig 3. Typical Transfer Characteristics

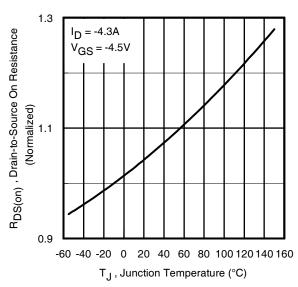


Fig 4. Normalized On-Resistance Vs. Temperature

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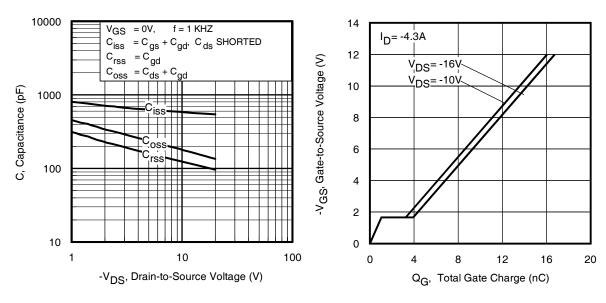


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

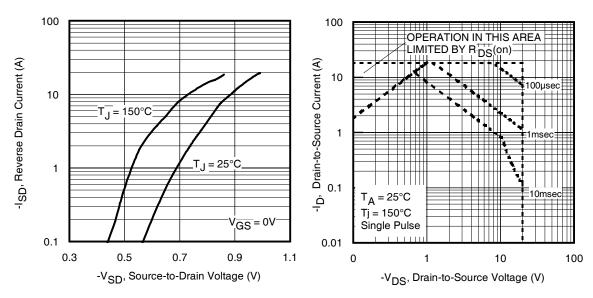


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

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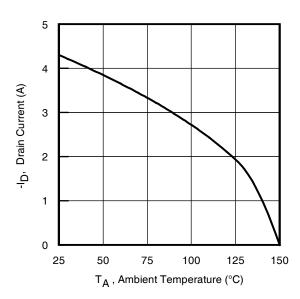


Fig 9. Maximum Drain Current Vs. Ambient Temperature

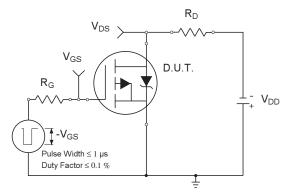


Fig 10a. Switching Time Test Circuit

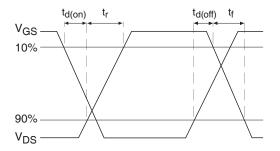


Fig 10b. Switching Time Waveforms

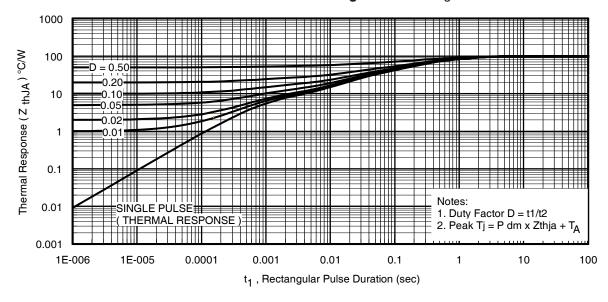
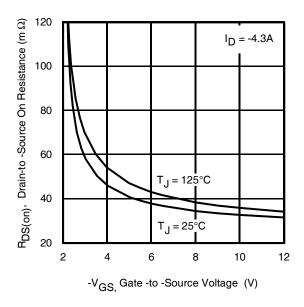


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

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200 $R_{\mbox{\footnotesize DS}}(\mbox{on}), \mbox{ Drain-to -Source On Resistance } (\mbox{$\mathfrak{m}\Omega$})$ 160 Vgs = -2.5V120 80 40 0 0 5 35 15 20 25 30 -I_D, Drain Current (A)

Fig 12. Typical On-Resistance Vs. Gate Voltage

Fig 13. Typical On-Resistance Vs. Drain Current

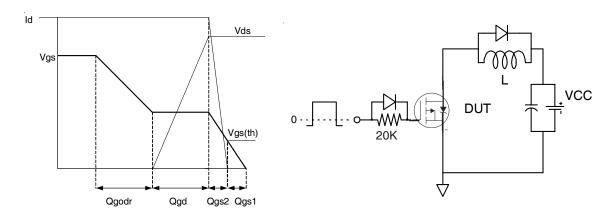


Fig 14a. Basic Gate Charge Waveform

Fig 14b. Gate Charge Test Circuit

International **IOR** Rectifier

IRLML2244TRPbF

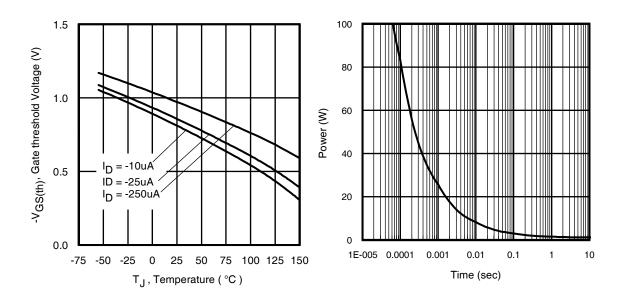


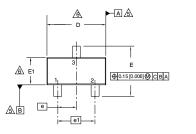
Fig 15. Typical Threshold Voltage Vs. Junction Temperature

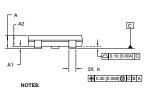
Fig 16. Typical Power Vs. Time

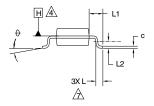


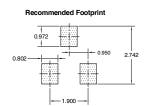
Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)









DIMENSIONS					
SYMBOL	MILLIM	ETERS	INCHES		
STIVIDOL	MIN	MAX	MIN	MAX	
Α	0.89	1.12	0.035	0.044	
A1	0.01	0.10	0.0004	0.004	
A2	0.88	1.02	0.035	0.040	
b	0.30	0.50	0.012	0.020	
С	0.08	0.20	0.003	0.008	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E1	1.20	1.40	0.047	0.055	
е	0.95	BSC	0.037	BSC	
e1	1.90	BSC	0.075	BSC	
L	0.40	0.60	0.016	0.024	
L1	0.54	REF	0.021	REF	
L2	0.25	BSC	0.010	BSC	
0	0	8	0	8	

- 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]. 3. CONTROLLING DIMENSION: MILLIMETER.
- A CONTROLLING DIMENSION MILLIMETER.

 ADATUM PLANE HIS LOCATED AT THE MOLD PARTING LINE.

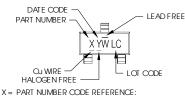
 ADATUM AND B TO BE DETERMINED AT DATUM PLANE H.

 ADMENSIONS D AND E1 ARE MEASUPED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLIDE MOLD PROTINGIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM [0.010 INCH] PER SIDE.

 ADMENSION LIS THE LEAD LEWISH FOR SOLDEFINIO TO A SUBSTRATE.

 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO 228 AB.

Micro3 (SOT-23/TO-236AB) Part Marking Information



W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Υ	WEEK	W	
2001	1	01	Α	
2002	2	02	В	
2003	3	03	С	
2004	4	04	D	
2005	5			
2006	6			
2007	7			
2008	8	1	1	
2009	9	y	7	
2010	0	24	X	
		25	Υ	
		26	Z	

A= IRLML2402 S = IRLML6244B = IRLML2803 T = IRLML6246 C= IRLML6302 U = IRLML6344 D = IRLML5103 E = IRLML6402 F = IRLML6401 G= IRLML2502 Y = IRLML2246 Z = IRFML9244

V= IRLML6346 W = IRFML8244 X = IRLML2244

H = IRLML5203 I = IRLML0030 J = IRLML2030K = IRLML0100L = IRLML0060 M = IRLML0040 N = IRLML2060 P = IRLML9301

R = IRLML9303

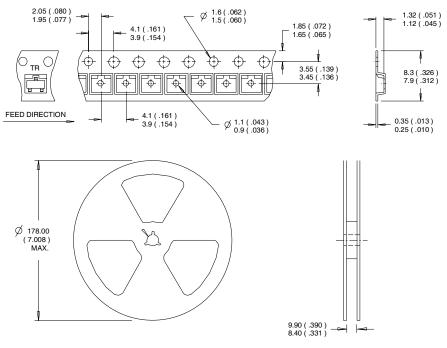
Note: A line above the work week (as shown here) indicates Lead - Free.

W = (27-52) IF PRECEDED BY ALETTER

YEAR	2 Y	WORK WEEK	W
2001	Α	27	Α
2002	В	28	В
2003	С	29	С
2004	D	30	D
2005	Ε		
2006	F		
2007	G		
2008	Н	1	1
2009	J	7	7
2010	K	50	Χ
		51	Υ
		52	Z

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Micro3TM Tape & Reel Information Dimensions are shown in millimeters (inches)



NOTES:

CONTROLLING DIMENSION : MILLIMETER.
 OUTLINE CONFORMS TO EIA-481 & EIA-541.

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TOR Rectifier

Orderable part number	Package Type	Standard Pack Note		Note
_		Form	Quantity	
IRLML2244TRPbF	Micro3	Tape and Reel	3000	

Qualification information[†]

Qualification level	Consumer ^{††} (per JEDEC JES D47F ^{†††} guidelines)		
	(per JEDEC JES D4/F guidelines)		
		MS L 1	
Moisture Sensitivity Level	Micro3	(per IPC/JEDEC J-STD-020D ^{†††})	
RoHS compliant	Yes		

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/product-info/reliability
- †† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: http://www.irf.com/whoto-call/salesrep/
- ††† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width \leq 400 μ s; duty cycle \leq 2%.
- 3 Surface mounted on 1 in square Cu board
- Refer to <u>application note #AN-994.</u>

Data and specifications subject to change without notice.



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